ASM3P2111A

Peak EMI Reducing Solution

Features

- Generates an EMI optimized clocking signal at output.
- Input frequency – 25 MHz.
- Frequency outputs:
  - 60 MHz (unmodulated)
  - 2 x 48 MHz (unmodulated)
  - 66.6 MHz (modulated) -1.7% down spread
- Modulation rate: 30 KHz.
- Supply voltage range: 3.3V ± 0.3V.
- Available in 8-pin SOIC Package.
- Commercial and Industrial Temperature range.

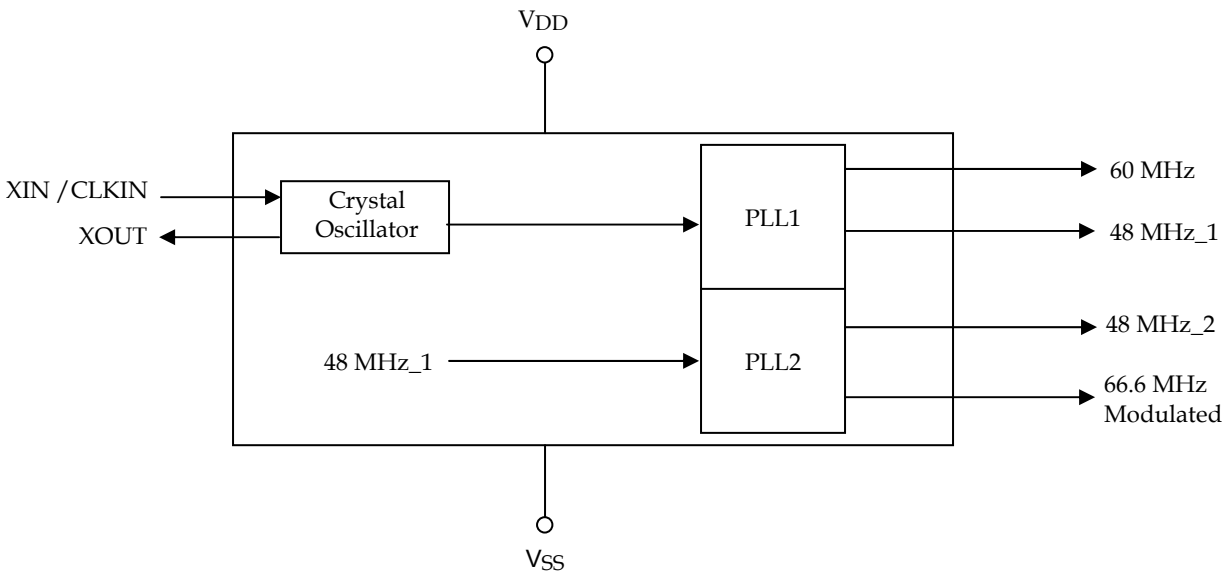
Product Description

The ASM3P2111A is a versatile spread spectrum frequency modulator. The ASM3P2111A reduces electromagnetic interference (EMI) at the clock source. The ASM3P2111A allows significant system cost savings by reducing the number of circuit board layers and shielding that are required to pass EMI regulations. The ASM3P2111A modulates the output of PLL in order to spread the bandwidth of a synthesized clock, thereby decreasing the peak amplitudes of its harmonics. This results in significantly lower system EMI compared to the typical narrow band signal produced by oscillators and most clock generators. Lowering EMI by increasing a signal's bandwidth is called spread spectrum clock generation.

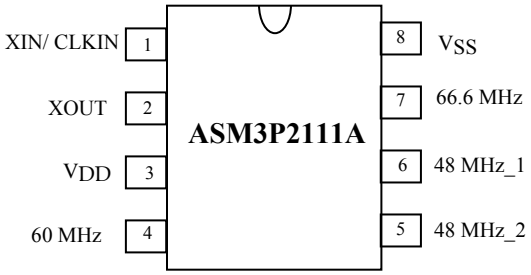
Applications

ASM3P2111A is targeted towards EMI management for high speed digital applications such as PC peripheral devices, consumer electronics and embedded controller systems.

Block Diagram



Pin Configuration



Pin Description

Pin Name	Type	Description
XIN / CLKIN	I	Connection to crystal
XOUT	O	Connection to crystal
V_{DD}	P	Power supply for the analog and digital blocks(+3.3V)
60 MHz	O	Clock output-1 60 MHz unmodulated
48 MHz_2	O	Clock output-2 48 MHz_2 unmodulated
48 MHz_1	O	Clock output-3 48 MHz_1 unmodulated
66.6 MHz	O	Clock output-4 66.6 MHz modulated
V_{SS}	P	Ground to entire chip

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
V_{DD}, V_{IN}	Voltage on any pin with respect to Ground	-0.5 to +7.0	V
T_{STG}	Storage temperature	-65 to +125	°C
T_A	Operating temperature	0 to 70	°C
T_s	Max. Soldering Temperature (10 sec)	260	°C
T_J	Junction Temperature	150	°C
T_{DV}	Static Discharge Voltage (As per JEDEC STD 22- A114-B)	2	KV

Note: These are stress ratings only and are not implied for functional use. Exposure to absolute maximum ratings for prolonged periods of time may affect device reliability.

Operating Conditions

Parameter	Symbol	Condition / Description	Min	Typ	Max	Unit
Supply Voltage	V_{DD}	3.3V ± 0.3V	3	3.3	3.6	V
Crystal Resonator Frequency	F_{XIN}		25	-	-	MHz
Output Driver Load Capacitance	C_L		-	-	15	pF

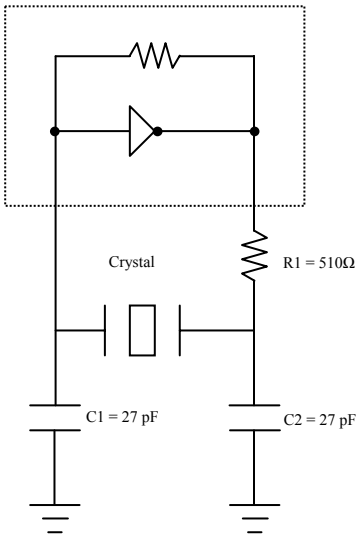
DC Electrical Characteristics

Parameter	Symbol	Conditions / Description	Min	Typ	Max	Unit
Overall						
Supply Current, Dynamic	I_{DD}	V_{DD}=3.3V, F_{CLK}=25MHz, C_L=15pF	41	48	62	mA
Supply Current, Static	I_{DDL}	V_{DD} = 3.3V, Clock Input = 0	20	25	35	mA
All input pins						
High-Level Input Voltage	V_{IH}	V_{DD}=3.3V	2.0	-	V_{DD}+0.3	V
Low-Level Input Voltage	V_{IL}	V_{DD}=3.3V	V_{SS}-0.3	-	0.8	V
High-Level Input Current	I_{IH}		-1	-	1	μA
Low-Level Input Current (pull-up)	I_{IL}		-20	-36	-80	μA
High-Level Output Source Current	I_{xOH}	V_{DD}=V (XIN) = 3.3V, V_O=0.4V	-	3	-	mA
Low-Level Output Sink Current	I_{xOL}	V_{DD}=3.3V, V (XIN)=V_O=2.5V	-	3	-	mA
Clock Outputs						
High-Level Output Source Current	I_{OH}	V_O=2.5V	-	-20	-	mA
Low-Level Output Sink Current	I_{OL}	V_O=0.4V	-	23	-	mA
Output Impedance	Z_{OH}	V_O=0.5V_{DD}; output driving high	-	29	-	Ω
	Z_{OL}	Vo=0.5V_{DD}; output driving low	-	27	-	

AC Electrical Characteristics

Parameter	Symbol	Conditions/ Description	Min	Typ	Max	Unit
Rise Time	t_r	V_O = 0.8V to 2.0V; C_L = 15pF	300	800	900	pS
Fall Time	t_f	V_O = 2.0V to 0.8V; C_L = 15pF	360	800	900	pS
Clock Duty Cycle		Ratio of pulse width (as measured from rising edge to next falling edge at 2.5V) to one clock period	45	-	55	%
* CL = 15 pF, Input clock frequency = 25 MHz						

Crystal Oscillator Circuit

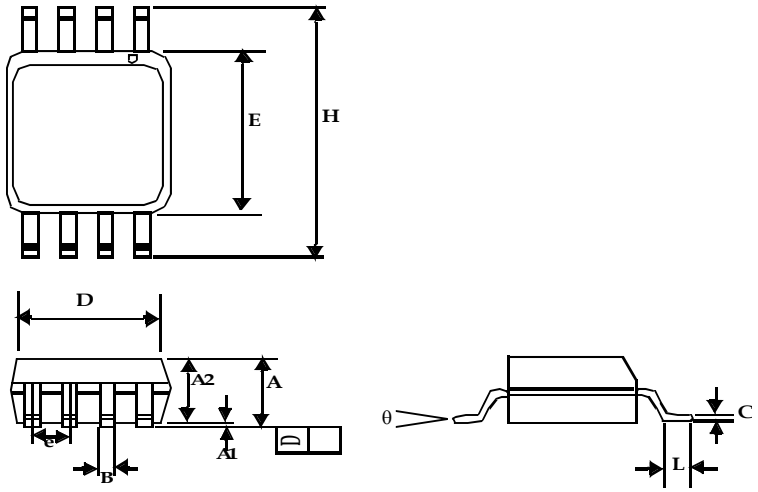


Crystal Specifications

Fundamental AT cut parallel resonant crystal	
Nominal frequency	25 MHz
Frequency tolerance	± 50 ppm or better at 25°C
Operating temperature range	-25°C to +85°C
Storage temperature	-40°C to +85°C
Load capacitance	18pF
Shunt capacitance	7pF maximum
ESR	25 Ω

Package Information

8-Pin SOIC Package

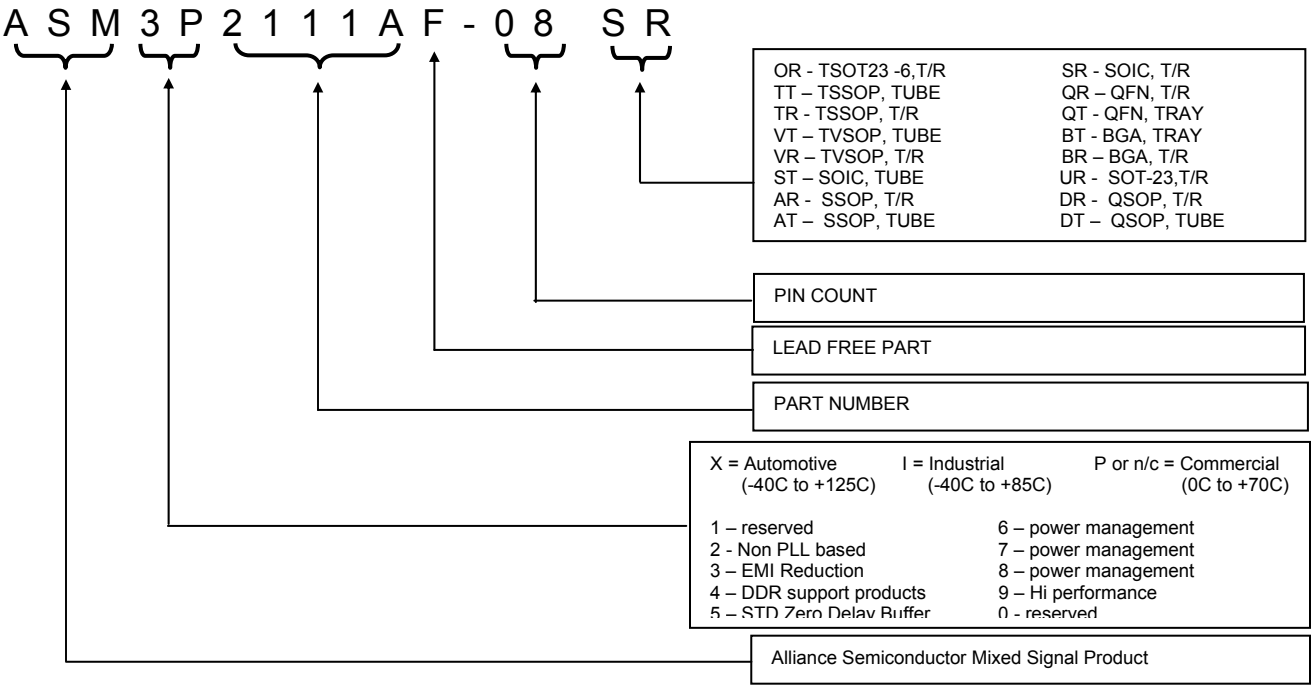


Symbol	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
A1	0.004	0.010	0.10	0.25
A	0.053	0.069	1.35	1.75
A2	0.049	0.059	1.25	1.50
B	0.012	0.020	0.31	0.51
C	0.007	0.010	0.18	0.25
D	0.193 BSC		4.90 BSC	
E	0.154 BSC		3.91 BSC	
e	0.050 BSC		1.27 BSC	
H	0.236 BSC		6.00 BSC	
L	0.016	0.050	0.41	1.27
θ	0°	8°	0°	8°

Ordering Codes

Part number	MARKING	Package Configuration	Temperature Range
ASM3P2111AF-08ST	3P2111AF	8-pin SOIC TUBE, Pb Free	Commercial
ASM3P2111AF-08SR	3P2111AF	8-pin SOIC TAPE & REEL, Pb Free	Commercial
ASM3I2111AF-08ST	3I2111AF	8-pin SOIC TUBE, Pb Free	Industrial
ASM3I2111AF-08SR	3I2111AF	8-pin SOIC TAPE & REEL, Pb Free	Industrial

Ordering Information



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Note: This product utilizes US Patent # 6,646,463 Impedance Emulator Patent issued to Alliance Semiconductor, dated 11-11-2003